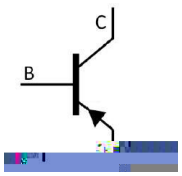
WR0<50P ṂṂÞ SQS ÆṀч s ll ㄱ Silicon PNP transistor in a TO-92LM Plastic Package.

лъ 5VG99:+D,Ӣ´
Complementary pair with 2SD667(A).

ᵮ Ӈ ļ ı ' ѽ ᶻ
Low frequency power amplifier.

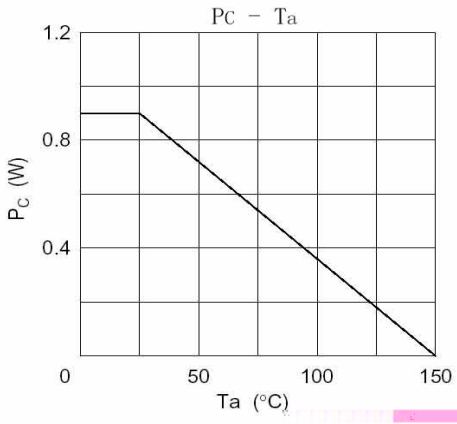


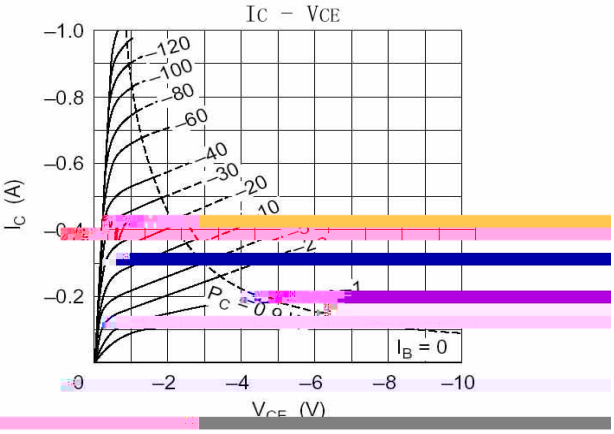


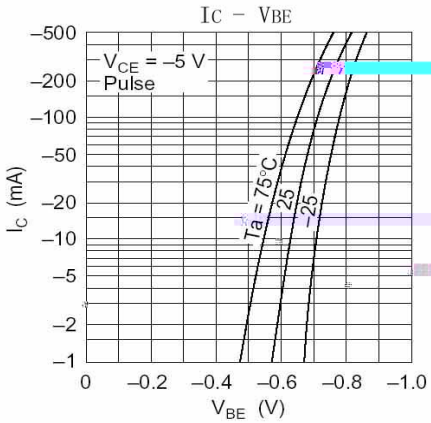
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

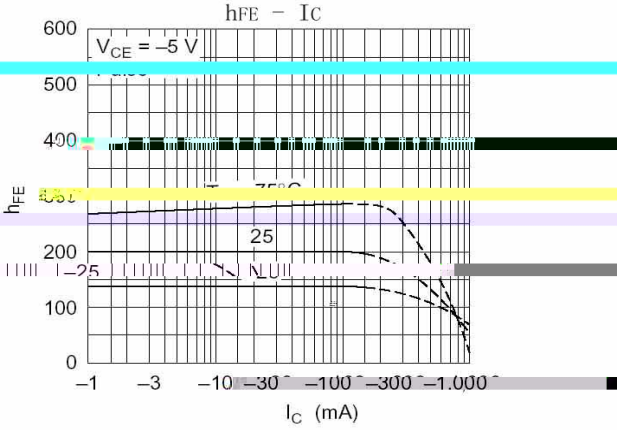
v Ѽ Parameter	ϒ N Symbol		Ѽ Ө Rating	D Ң Unit
Collector to Base Voltage	V_{CBO}		-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647	-80	V
		2SB647A	-100	
Emitter to Base Voltage	V_{EBO}		-5.0	V
Collector Current (DC)	I_C		-1.0	A
Collector Current(Pulse)	I_{CP}		-2.0	A
Collector Power Dissipation	P_C		900	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T			

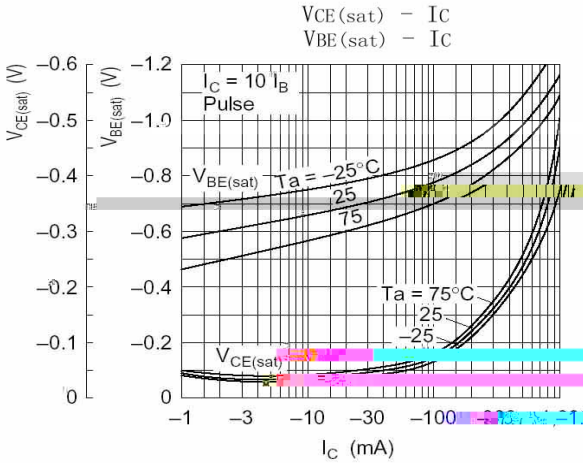
/ Electrical Characteristic Curve

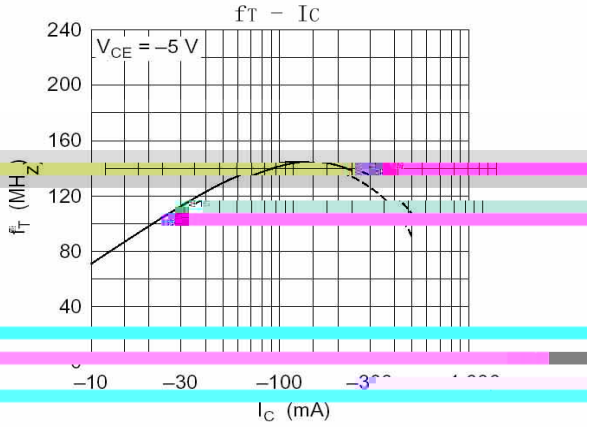






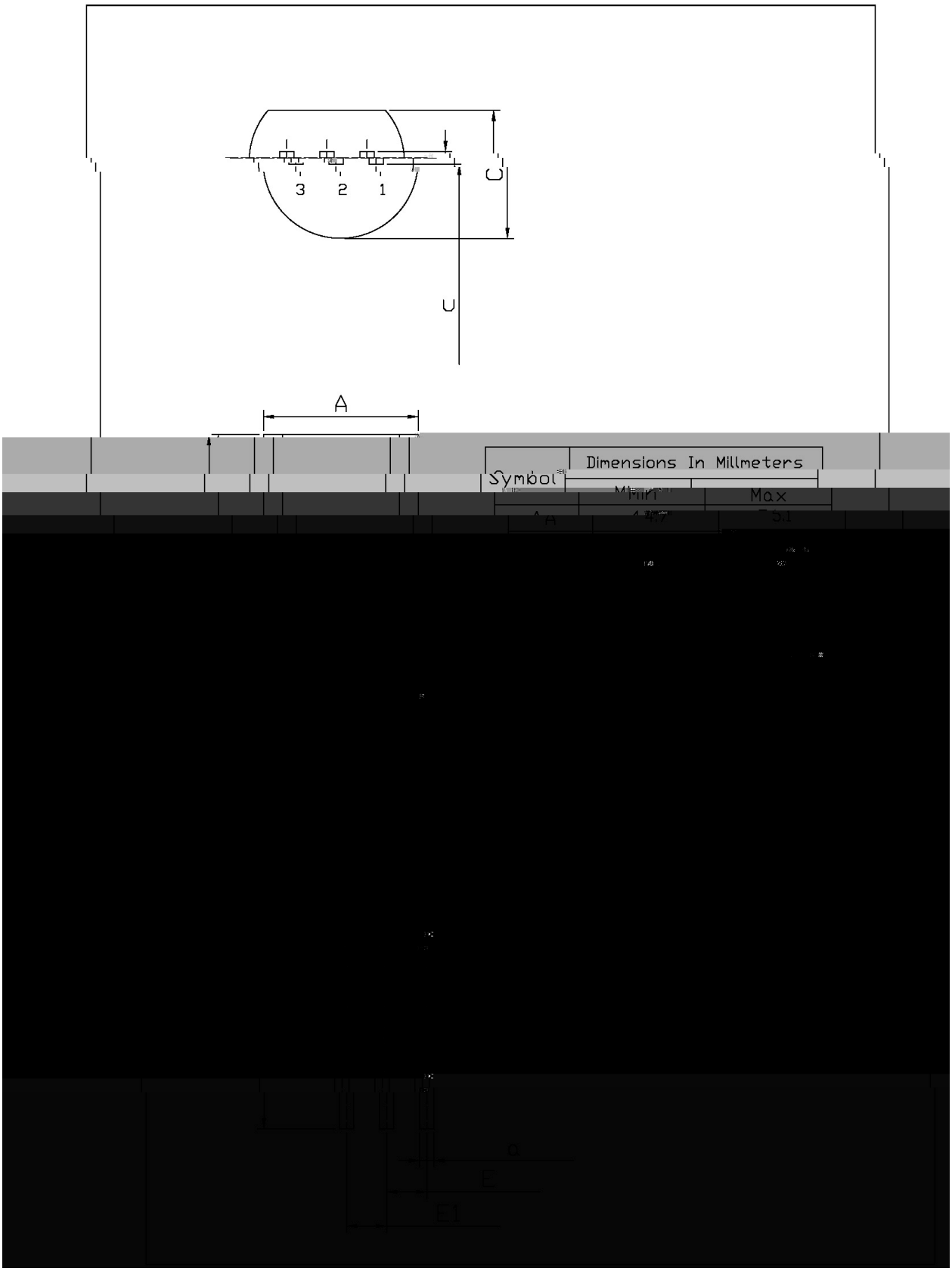




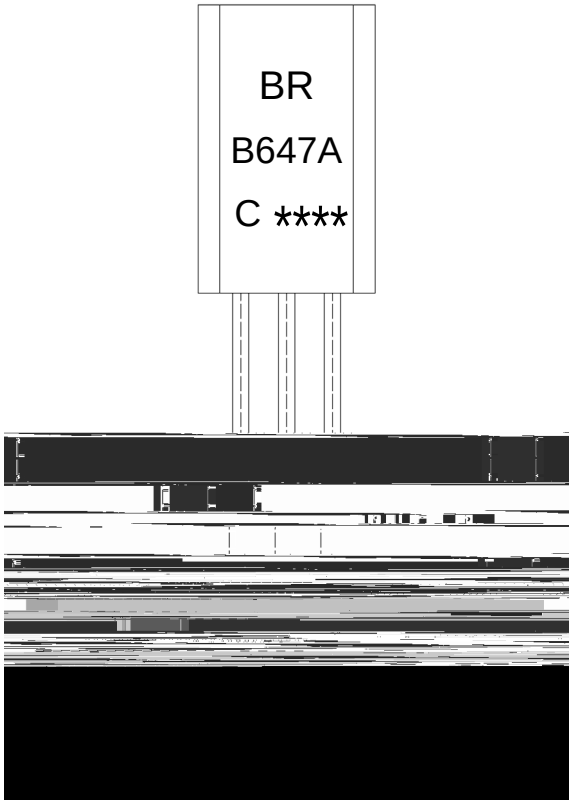


/ Package Dimensions

TO-92LM Unit: mm



/ Marking Instructions



ب ″ χ	
EU=	₩ ३ И Ґђ
E97 : D χ	₩ ʒ ᴺ Ґђ
F=	₩ k ᵢₕ ʿ ⁶ Ґђ
---- χ	₩ ł ғ ń ᴺ Ґђ ı ₰ ł ғ ń ᴺ Ψ ק

Note:

BR:	Company Code.
B647A:	Product Type.
C:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ɬ , Time:60~6Tc2 18 re7.Tf1.6f150est